

### Low Distortion Internally Matched Power GaAs FETs (C-Band)

#### Features

- Low intermodulation distortion
  - $IM_3 = -45$  dBc at  $P_o = 28$  dBm,
  - Single carrier level
- High power
  - $P_{1dB} = 39$  dBm at 5.9 GHz to 6.4 GHz
- High gain
  - $G_{1dB} = 9.0$  dB at 5.9 GHz to 6.4 GHz
- Broad band internally matched
- Hermetically sealed package

#### RF Performance Specifications (Ta = 25° C)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	$P_{1dB}$	$V_{DS} = 10V$ $f = 5.9 \sim 6.4$ GHz	dBm	38.0	39.0	–
Power Gain at 1dB Compression Point	$G_{1dB}$		dB	8.0	9.0	–
Drain Current	$I_{DS1}$		A	–	2.1	2.6
Gain Flatness	$\Delta G$		dB	–	–	$\pm 0.6$
Power Added Efficiency	$\eta_{add}$		%	–	33	–
3rd Order Intermodulation Distortion	$IM_3$	Note 1	dBc	-42	-45	–
Drain Current	$I_{DS2}$		A	–	2.1	2.6
Channel-Temperature Rise	$\Delta T_{ch}$	$V_{DS} \times I_{DS} \times R_{th}(c-c)$	°C	–	–	80

#### Electrical Characteristics (Ta = 25° C)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 2.6A$	mS	–	1600	–
Pinch-off Voltage	$V_{GSoff}$	$V_{DS} = 3V$ $I_{DS} = 35mA$	V	-2	-3.5	-5.0
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	5.0	6.5
Gate-Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -105\mu A$	V	-5	–	–
Thermal Resistance	$R_{th}(c-c)$	Channel to case	°C/W	–	3.6	4.8

Note 1: 2 tone Test Pout = 28.5dBm Single Carrier Level.

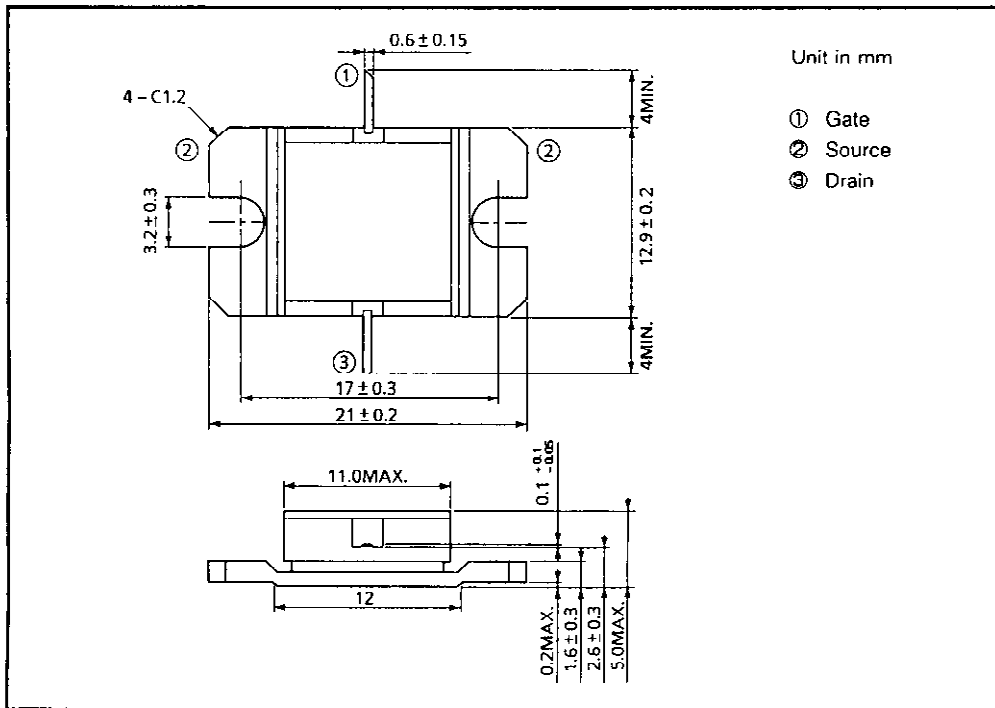
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**Absolute Maximum Ratings (Ta = 25° C)**

Characteristic	Symbol	Unit	Rating
Drain-Source Voltage	$V_{DS}$	V	15
Gate-Source Voltage	$V_{GS}$	V	-5
Drain Current	$I_{DS}$	A	6.5
Total Power Dissipation (T <sub>c</sub> = 25°C)	P <sub>T</sub>	W	30
Channel Temperature	T <sub>ch</sub>	°C	175
Storage Temperature	T <sub>stg</sub>	°C	-65~175

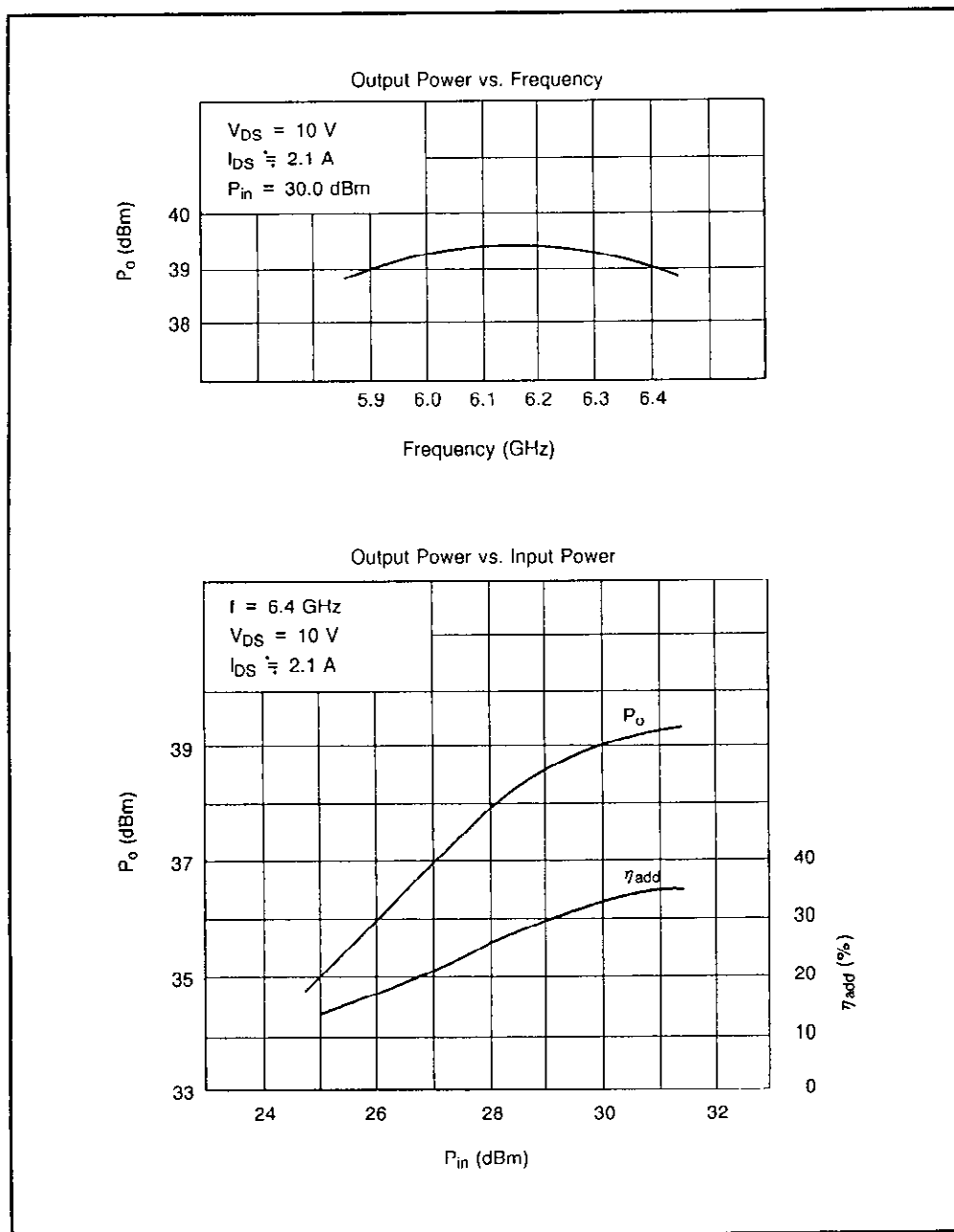
**Package Outline (2-11D1B)**



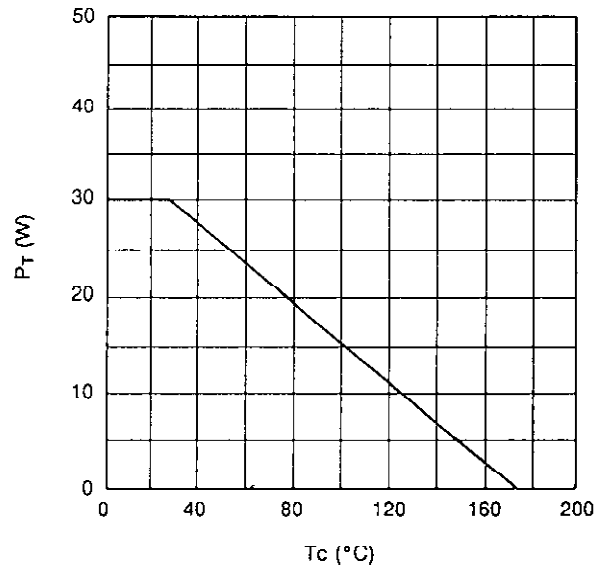
**Handling Precautions for Packaged Type**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

## RF Performances



Power Dissipation vs. Case Temperature



$IM_3$  vs. Output Power Characteristics

